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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	
Number of Logic Elements/Cells	·
Total RAM Bits	110592
Number of I/O	235
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p600l-fg484i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

## Microsemi

FPGA Array Architecture in Low Power Flash Devices

## **FPGA Array Architecture Support**

The flash FPGAs listed in Table 1-1 support the architecture features described in this document.

#### Table 1-1 • Flash-Based FPGAs

Series	Family <sup>*</sup>	Description
IGLOO <sup>®</sup>	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC <sup>®</sup> 3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM <sup>®</sup> Cortex <sup>™</sup> -M1 soft processors, and flash memory into a monolithic device

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 1-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 1-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

 There will be added skew and clock insertion delay due to the clock gating circuit. The user should analyze external setup/hold times carefully. The user should also ensure the additional skew across the clock gating filter circuit is accounted for in any paths where the launch register is driven from the filter input clock and captured by a register driven by the gated clock filter output clock.

#### **Power Analysis**

SmartPower identifies static and dynamic power consumption problems quickly within a design. It provides a hierarchical view, allowing users to drill down and estimate the power consumption of individual components or events. SmartPower analyzes power consumption for nets, gates, I/Os, memories, clocks, cores, clock domains, power supply rails, peak power during a clock cycle, and switching transitions.

SmartPower generates detailed hierarchical reports of the dynamic power consumption of a design for easy inspection. These reports include design-level power summary, average switching activity, and ambient and junction temperature readings. Enter the target clock and data frequencies for a design, and let SmartPower perform a detailed and accurate power analysis. SmartPower supports importing files in the VCD (Value-Change Dump) format as specified in the IEEE 1364 standard. It also supports the Synopsys<sup>®</sup> Switching Activity Interchange Format (SAIF) standard. Support for these formats lets designers generate switching activity information in a variety of simulators and then import this information directly into SmartPower.

For portable or battery-operated applications, a power profile feature enables you to measure power and battery life, based on a sequence of operational modes of the design. In most portable and battery-operated applications, the system is seldom fully "on" 100 percent of the time. "On" is a combination of fully active, standby, sleep, or other functional modes. SmartPower allows users to create a power profile for a design by specifying operational modes and the percent of time the device will run in each of the modes. Power is calculated for each of the modes, and total power is calculated based on the weighted average of all modes.

SmartPower also provides an estimated battery life based on the power profile. The current capacity for a given battery is entered and used to estimate the life of the battery. The result is an accurate and realistic indication of battery life.

More information on SmartPower can be found on the Microsemi SoC Products Group website: http://www.microsemi.com/soc/products/software/libero/smartpower.aspx.

### **Additional Power Conservation Techniques**

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 FPGAs provide many ways to inherently conserve power; however, there are also several design techniques that can be used to reduce power on the board.

- Microsemi recommends that the designer use the minimum number of I/O banks possible and tie any unused power supplies (such as V<sub>CCPLL</sub>, V<sub>CCI</sub>, VMV, and V<sub>PUMP</sub>) to ground.
- Leave unused I/O ports floating. Unused I/Os are configured by the software as follows:
  - Output buffer is disabled (with tristate value of high impedance)
  - Input buffer is disabled (with tristate value of high impedance)
- Use the lowest available voltage I/O standard, the lowest drive strength, and the slowest slew rate to reduce I/O switching contribution to power consumption.
- Advanced and pro I/O banks may consume slightly higher static current than standard and standard plus banks—avoid using advanced and pro banks whenever practical.
  - The small static power benefit obtained by avoiding advanced or pro I/O banks is usually negligible compared to the benefit of using a low power I/O standard.
- Deselect RAM blocks that are not being used.
- Only enable read and write ports on RAM blocks when they are needed.
- Gating clocks LOW offers improved static power of RAM blocks.
- Drive the FF port of RAM blocks with the Flash\_Freeze\_Enabled signal from the Flash\*Freeze management IP.
- Drive inputs to the full voltage level so that all transistors are turned on or off completely.

## **Microsemi**.

Global Resources in Low Power Flash Devices

Date	Changes	Page
v1.1 (March 2008)	The "Global Architecture" section was updated to include the IGLOO PLUS family. The bullet was revised to include that the west CCC does not contain a PLL core in 15 k and 30 k devices. Instances of "A3P030 and AGL030 devices" were replaced with "15 k and 30 k gate devices."	47
v1.1 (continued)	Table 3-1 • Flash-Based FPGAs and the accompanying text was updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	48
	The "VersaNet Global Network Distribution" section, "Spine Architecture" section, the note in Figure 3-1 • Overview of VersaNet Global Network and Device Architecture, and the note in Figure 3-3 • Simplified VersaNet Global Network (60 k gates and above) were updated to include mention of 15 k gate devices.	49, 50
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to add the A3P015 device, and to revise the values for clock trees, globals/spines per tree, and globals/spines per device for the A3P030 and AGL030 devices.	57
	Table 3-5 • Globals/Spines/Rows for IGLOO PLUS Devices is new.	58
	CLKBUF_LVCMOS12 was added to Table 3-9 • I/O Standards within CLKBUF.	63
	The "User's Guides" section was updated to include the three different I/O Structures chapters for ProASIC3 and IGLOO device families.	74
v1.0 (January 2008)	Figure 3-3 • Simplified VersaNet Global Network (60 k gates and above) was updated.	50
	The "Naming of Global I/Os" section was updated.	51
	The "Using Global Macros in Synplicity" section was updated.	66
	The "Global Promotion and Demotion Using PDC" section was updated.	67
	The "Designer Flow for Global Assignment" section was updated.	69
	The "Simple Design Example" section was updated.	71
51900087-0/1.05 (January 2005)	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated.	57

# 5 – FlashROM in Microsemi's Low Power Flash Devices

## Introduction

The Fusion, IGLOO, and ProASIC3 families of low power flash-based devices have a dedicated nonvolatile FlashROM memory of 1,024 bits, which provides a unique feature in the FPGA market. The FlashROM can be read, modified, and written using the JTAG (or UJTAG) interface. It can be read but not modified from the FPGA core. Only low power flash devices contain on-chip user nonvolatile memory (NVM).

## Architecture of User Nonvolatile FlashROM

Low power flash devices have 1 kbit of user-accessible nonvolatile flash memory on-chip that can be read from the FPGA core fabric. The FlashROM is arranged in eight banks of 128 bits (16 bytes) during programming. The 128 bits in each bank are addressable as 16 bytes during the read-back of the FlashROM from the FPGA core. Figure 5-1 shows the FlashROM logical structure.

The FlashROM can only be programmed via the IEEE 1532 JTAG port. It cannot be programmed directly from the FPGA core. When programming, each of the eight 128-bit banks can be selectively reprogrammed. The FlashROM can only be reprogrammed on a bank boundary. Programming involves an automatic, on-chip bank erase prior to reprogramming the bank. The FlashROM supports synchronous read. The address is latched on the rising edge of the clock, and the new output data is stable after the falling edge of the same clock cycle. For more information, refer to the timing diagrams in the DC and Switching Characteristics chapter of the appropriate datasheet. The FlashROM can be read on byte boundaries. The upper three bits of the FlashROM address from the FPGA core define the bank being accessed. The lower four bits of the FlashROM address from the FPGA core define which of the 16 bytes in the bank is being accessed.

		Byte Number in Bank							4 LSB of ADDR (READ)									
		15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0	
of	7																	
3 MSB of EAD)	6																	
ΑD	5																	
er 🕄	4																	
dr (	3																	
ADI Nu	2																	
Bank Number 3 MS ADDR (READ)	1																	
ä	0																	

Figure 5-1 • FlashROM Architecture



I/O Structures in IGLOO and ProASIC3 Devices

### I/O Bank Structure

Low power flash device I/Os are divided into multiple technology banks. The number of banks is devicedependent. The IGLOOe, ProASIC3EL, and ProASIC3E devices have eight banks (two per side); and IGLOO, ProASIC3L, and ProASIC3 devices have two to four banks. Each bank has its own V**CCI** power supply pin. Multiple I/O standards can co-exist within a single I/O bank.

In IGLOOe, ProASIC3EL, and ProASIC3E devices, each I/O bank is subdivided into VREF minibanks. These are used by voltage-referenced I/Os. VREF minibanks contain 8 to 18 I/Os. All I/Os in a given minibank share a common VREF line (only one VREF pin is needed per VREF minibank). Therefore, if an I/O in a VREF minibank is configured as a VREF pin, the remaining I/Os in that minibank will be able to use the voltage assigned to that pin. If the location of the VREF pin is selected manually in the software, the user must satisfy VREF rules (refer to the "I/O Software Control in Low Power Flash Devices" section on page 251). If the user does not pick the VREF pin manually, the software automatically assigns it.

Figure 7-3 is a snapshot of a section of the I/O ring, showing the basic elements of an I/O tile, as viewed from the Designer place-and-route tool's MultiView Navigator (MVN).

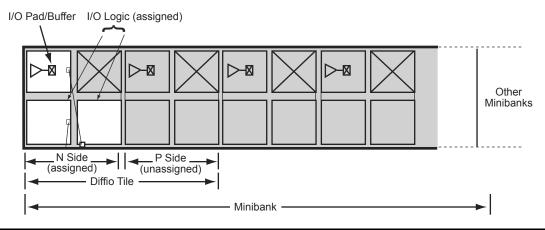


Figure 7-3 • Snapshot of an I/O Tile

Low power flash device I/Os are implemented using two tile types: I/O and differential I/O (diffio).

The diffio tile is built up using two I/O tiles, which form an I/O pair (P side and N side). These I/O pairs are used according to differential I/O standards. Both the P and N sides of the diffio tile include an I/O buffer and two I/O logic blocks (auxiliary and main logic).

Every minibank (E devices only) is built up from multiple diffio tiles. The number of the minibank depends on the different-size dies. Refer to the "I/O Architecture" section on page 181 for an illustration of the minibank structure.

Figure 7-4 on page 183 shows a simplified diagram of the I/O buffer circuitry. The Output Enable signal (OE) enables the output buffer to pass the signal from the core logic to the pin. The output buffer contains ESD protection circuitry, an n-channel transistor that shunts all ESD surges (up to the limit of the device ESD specification) to GND. This transistor also serves as an output pull-down resistor.

Each output buffer also contains programmable slew rate, drive strength, programmable power-up state (pull-up/-down resistor), hot-swap, 5 V tolerance, and clamp diode control circuitry. Multiple flash switches (not shown in Figure 7-4 on page 183) are programmed by user selections in the software to activate different I/O features.

#### Table 7-8 • Hot-Swap Level 1

Description	Cold-swap
Power Applied to Device	No
Bus State	-
Card Ground Connection	-
Device Circuitry Connected to Bus Pins	-
Example Application	System and card with Microsemi FPGA chip are powered down, and the card is plugged into the system. Then the power supplies are turned on for the system but not for the FPGA on the card.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices: Compliant Other IGLOO/ProASIC3 devices: Compliant if bus switch used to isolate FPGA I/Os from rest of system IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode.

Table 7-9 • Hot-Swap Level 2

Description	Hot-swap while reset
Power Applied to Device	Yes
Bus State	Held in reset state
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	-
Example Application	In the PCI hot-plug specification, reset control circuitry isolates the card busses until the card supplies are at their nominal operating levels and stable.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode. Other IGLOO/ProASIC3 devices: Compliant

#### Solution 4

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

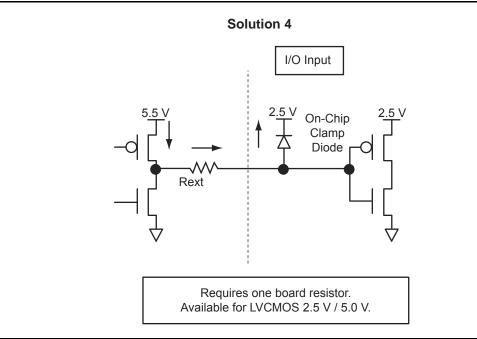


Figure 7-12 • Solution 4

## Microsemi

I/O Structures in IGLOOe and ProASIC3E Devices

#### Table 8-9 • Hot-Swap Level 1

Description	Cold-swap
Power Applied to Device	No
Bus State	-
Card Ground Connection	-
Device Circuitry Connected to Bus Pins	-
Example Application	System and card with Microsemi FPGA chip are powered down, and the card is plugged into the system. Then the power supplies are turned on for the system but not for the FPGA on the card.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices: Compliant Other IGLOO/ProASIC3 devices: Compliant if bus switch used to isolate FPGA I/Os from rest of system IGLOOe/ProASIC3E devices: Compliant I/Os can, but do not have to be set to hot-insertion mode.

Table 8-10 • Hot-Swap Level 2

Description	Hot-swap while reset
Power Applied to Device	Yes
Bus State	Held in reset state
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	-
Example Application	In the PCI hot-plug specification, reset control circuitry isolates the card busses until the card supplies are at their nominal operating levels and stable.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode. Other IGLOO/ProASIC3 devices: Compliant

This current draw can occur in the following cases:

- In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash\*Freeze mode:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

### **Electrostatic Discharge Protection**

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All IGLOO and ProASIC3 devices are tested to the Human Body Model (HBM) and the Charged Device Model (CDM).

Each I/O has two clamp diodes. One diode has its positive (P) side connected to the pad and its negative (N) side connected to VCCI. The second diode has its P side connected to GND and its N side connected to the pad. During operation, these diodes are normally biased in the off state, except when transient voltage is significantly above VCCI or below GND levels.

In 30 k gate devices, the first diode is always off. In other devices, the clamp diode is always on and cannot be switched off.

By selecting the appropriate I/O configuration, the diode is turned on or off. Refer to Table 8-13 for more information about the I/O standards and the clamp diode.

The second diode is always connected to the pad, regardless of the I/O configuration selected.

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTL/LVCMOS	No	Yes	Yes <sup>1</sup>	Enabled	/Disabled
3.3 V PCI, 3.3 V PCI-X	Yes	No	Yes <sup>1</sup>	Enabled	/Disabled
LVCMOS 2.5 V <sup>2</sup>	No	Yes	No	Enabled/Disabled	
LVCMOS 2.5 V / 5.0 V <sup>2</sup>	Yes	No	Yes <sup>3</sup>	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
Voltage-Referenced Input Buffer	No	Yes	No	Enabled/Disabled	
Differential, LVDS/B-LVDS/M-LVDS/LVPECL	No	Yes	No	Enabled	/Disabled

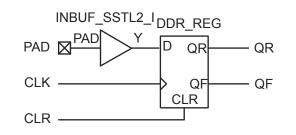
#### Table 8-13 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOOe and ProASIC3E Devices

Notes:

1. Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.

- In the SmartGen Core Reference Guide, select the LVCMOS5 macro for the LVCMOS 2.5 V / 5.0 V I/O standard or the LVCMOS25 macro for the LVCMOS 2.5 V I/O standard.
- 3. Can be implemented with an external resistor and an internal clamp diode.

### **DDR Input Register**



#### Figure 10-5 • DDR Input Register (SSTL2 Class I)

The corresponding structural representations, as generated by SmartGen, are shown below:

#### Verilog

```
module DDR_InBuf_SSTL2_I(PAD,CLR,CLK,QR,QF);
```

input PAD, CLR, CLK; output QR, QF; wire Y; INBUF\_SSTL2\_I INBUF\_SSTL2\_I\_0\_inst(.PAD(PAD),.Y(Y));

DDR\_REG\_DDR\_REG\_0\_inst(.D(Y),.CLK(CLK),.CLR(CLR),.QR(QR),.QF(QF));

endmodule

#### VHDL

```
library ieee;
use ieee.std_logic_1164.all;
--The correct library will be inserted automatically by SmartGen
library proasic3; use proasic3.all;
--library fusion; use fusion.all;
--library igloo; use igloo.all;
entity DDR_InBuf_SSTL2_I is
  port(PAD, CLR, CLK : in std_logic; QR, QF : out std_logic) ;
end DDR_InBuf_SSTL2_I;
architecture DEF_ARCH of DDR_InBuf_SSTL2_I is
  component INBUF_SSTL2_I
    port(PAD : in std_logic := 'U'; Y : out std_logic) ;
  end component;
  component DDR_REG
   port(D, CLK, CLR : in std_logic := 'U'; QR, QF : out std_logic) ;
  end component;
signal Y : std_logic ;
begin
  INBUF_SSTL2_I_0_inst : INBUF_SSTL2_I
  port map(PAD => PAD, Y => Y);
  DDR_REG_0_inst : DDR_REG
  port map(D => Y, CLK => CLK, CLR => CLR, QR => QR, QF => QF);
end DEF_ARCH;
```



DDR for Microsemi's Low Power Flash Devices

```
DDR_OUT_0_inst : DDR_OUT
port map(DR => DataR, DF => DataF, CLK => CLK, CLR => CLR, Q => Q);
TRIBUFF_F_8U_0_inst : TRIBUFF_F_8U
port map(D => Q, E => TrienAux, PAD => PAD);
```

end DEF\_ARCH;

### **DDR Bidirectional Buffer**

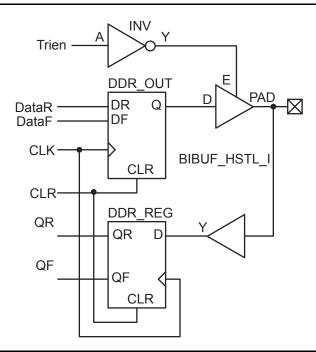


Figure 10-8 • DDR Bidirectional Buffer, LOW Output Enable (HSTL Class II)

#### Verilog

module DDR\_BiDir\_HSTL\_I\_LowEnb(DataR,DataF,CLR,CLK,Trien,QR,QF,PAD);

```
input DataR, DataF, CLR, CLK, Trien;
output QR, QF;
inout PAD;
wire TrienAux, D, Q;
INV Inv_Tri(.A(Trien), .Y(TrienAux));
DDR_OUT DDR_OUT_0_inst(.DR(DataR),.DF(DataF),.CLK(CLK),.CLR(CLR),.Q(Q));
DDR_REG DDR_REG_0_inst(.D(D),.CLK(CLK),.CLR(CLR),.QR(QR),.QF(QF));
BIBUF_HSTL_I BIBUF_HSTL_I_0_inst(.PAD(PAD),.D(Q),.E(TrienAux),.Y(D));
```

endmodule

#### Programming Centers

Microsemi programming hardware policy also applies to programming centers. Microsemi expects all programming centers to use certified programmers to program Microsemi devices. If a programming center uses noncertified programmers to program Microsemi devices, the "Noncertified Programmers" policy applies.

## **Important Programming Guidelines**

### **Preprogramming Setup**

Before programming, several steps are required to ensure an optimal programming yield.

#### Use Proper Handling and Electrostatic Discharge (ESD) Precautions

Microsemi FPGAs are sensitive electronic devices that are susceptible to damage from ESD and other types of mishandling. For more information about ESD, refer to the *Quality and Reliability Guide*, beginning with page 41.

#### Use the Latest Version of the Designer Software to Generate Your Programming File (recommended)

The files used to program Microsemi flash devices (\*.bit, \*.stp, \*.pdb) contain important information about the switches that will be programmed in the FPGA. Find the latest version and corresponding release notes at http://www.microsemi.com/soc/download/software/designer/. Also, programming files must always be zipped during file transfer to avoid the possibility of file corruption.

#### Use the Latest Version of the Programming Software

The programming software is frequently updated to accommodate yield enhancements in FPGA manufacturing. These updates ensure maximum programming yield and minimum programming times. Before programming, always check the version of software being used to ensure it is the most recent. Depending on the programming software, refer to one of the following:

- FlashPro: http://www.microsemi.com/soc/download/program\_debug/flashpro/
- · Silicon Sculptor: http://www.microsemi.com/soc/download/program\_debug/ss/

#### Use the Most Recent Adapter Module with Silicon Sculptor

Occasionally, Microsemi makes modifications to the adapter modules to improve programming yields and programming times. To identify the latest version of each module before programming, visit http://www.microsemi.com/soc/products/hardware/program\_debug/ss/modules.aspx.

#### Perform Routine Hardware Self-Diagnostic Test

- Adapter modules must be regularly cleaned. Adapter modules need to be inserted carefully into the programmer to make sure the DIN connectors (pins at the back side) are not damaged.
- FlashPro

The self-test is only applicable when programming with FlashPro and FlashPro3 programmers. It is not supported with FlashPro4 or FlashPro Lite. To run the self-diagnostic test, follow the instructions given in the "Performing a Self-Test" section of http://www.microsemi.com/soc/documents/FlashPro\_UG.pdf.

Silicon Sculptor

The self-diagnostic test verifies correct operation of the pin drivers, power supply, CPU, memory, and adapter module. This test should be performed with an adapter module installed and before every programming session. At minimum, the test must be executed every week. To perform self-diagnostic testing using the Silicon Sculptor software, perform the following steps, depending on the operating system:

- DOS: From anywhere in the software, type **ALT + D**.
- Windows: Click Device > choose Actel Diagnostic > select the Test tab > click OK.

Silicon Sculptor programmers must be verified annually for calibration. Refer to the *Silicon Sculptor Verification of Calibration Work Instruction* document on the website.

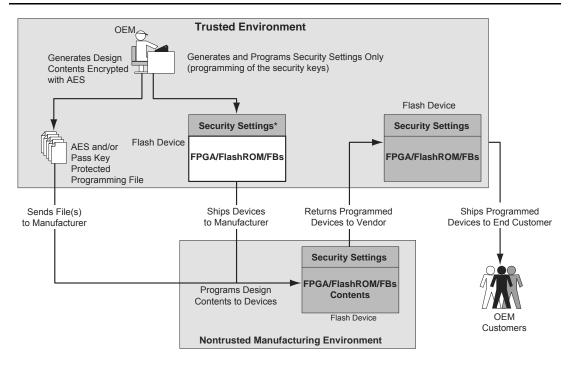
### Application 1: Trusted Environment

As illustrated in Figure 12-7, this application allows the programming of devices at design locations where research and development take place. Therefore, encryption is not necessary and is optional to the user. This is often a secure way to protect the design, since the design program files are not sent elsewhere. In situations where production programming is not available at the design location, programming centers (such as Microsemi In-House Programming) provide a way of programming designs at an alternative, secure, and trusted location. In this scenario, the user generates a STAPL programming file from the Designer software in plaintext format, containing information on the entire design or the portion of the design. Once the design is programmed to unprogrammed devices, the design is protected by this FlashLock Pass Key. If no future programming is needed, the user can consider permanently securing the IGLOO and ProASIC3 device, as discussed in the "Permanent FlashLock" section on page 307.

### **Application 2: Nontrusted Environment—Unsecured Location**

Often, programming of devices is not performed in the same location as actual design implementation, to reduce manufacturing cost. Overseas programming centers and contract manufacturers are examples of this scenario.

To achieve security in this case, the AES key and the FlashLock Pass Key can be initially programmed in-house (trusted environment). This is done by generating a programming file with only the security settings and no design contents. The design FPGA core, FlashROM, and (for Fusion) FB contents are generated in a separate programming file. This programming file must be set with the same AES key that was used to program to the device previously so the device will correctly decrypt this encrypted programming file. As a result, the encrypted design content programming file can be safely sent off-site to nontrusted programming locations for design programming. Figure 12-7 shows a more detailed flow for this application.



Notes:

1. Programmed portion indicated with dark gray.

2. Programming of FBs applies to Fusion only.

Figure 12-7 • Application 2: Device Programming in a Nontrusted Environment



Security in Low Power Flash Devices

Figure 12-10 • All Silicon Features Selected for IGLOO and ProASIC3 Devices

Figure 12-11 • All Silicon Features Selected for Fusion

## **Related Documents**

### **User's Guides**

FlashPro User's Guide

http://www.microsemi.com/soc/documents/flashpro\_ug.pdf

## **List of Changes**

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.5 (August 2009)	The "CoreMP7 Device Security" section was removed from "Security in ARM- Enabled Low Power Flash Devices", since M7-enabled devices are no longer supported.	304
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 12-1 • Flash-Based FPGAs.	302
v1.3 (October 2008)	The "Security Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	302
v1.2 (June 2008)	<ul> <li>The following changes were made to the family descriptions in Table 12-1 • Flash-Based FPGAs:</li> <li>ProASIC3L was updated to include 1.5 V.</li> <li>The number of PLLs for ProASIC3E was changed from five to six.</li> </ul>	302
v1.1 (March 2008)	The chapter was updated to include the IGLOO PLUS family and information regarding 15 k gate devices.	N/A
	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	302

# Microsemi

In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

Date	Changes	Page
July 2010 (continued)	The "Chain Integrity Test Error Analyze Chain Failure" section was renamed to the "Scan Chain Failure" section, and the Analyze Chain command was changed to Scan Chain. It was noted that occasionally a faulty programmer can cause scan chain failures.	338
v1.5 (August 2009)	The "CoreMP7 Device Security" section was removed from "Security in ARM- Enabled Low Power Flash Devices", since M7-enabled devices are no longer supported.	331
v1.4 (December 2008)	The "ISP Architecture" section was revised to include information about core voltage for IGLOO V2 and ProASIC3L devices, as well as 50 mV increments allowable in Designer software.	327
	IGLOO nano and ProASIC3 nano devices were added to Table 13-1 • Flash-Based FPGAs Supporting ISP.	328
	A second capacitor was added to Figure 13-6 • Board Layout and Programming Header Top View.	337
v1.3 (October 2008)	The "ISP Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	328
v1.2 (June 2008)	<ul> <li>The following changes were made to the family descriptions in Table 13-1 • Flash-Based FPGAs Supporting ISP:</li> <li>ProASIC3L was updated to include 1.5 V.</li> </ul>	328
	The number of PLLs for ProASIC3E was changed from five to six.	
v1.1 (March 2008)	The "ISP Architecture" section was updated to included the IGLOO PLUS family in the discussion of family-specific support. The text, "When 1.2 V is used, the device can be reprogrammed in-system at 1.5 V only," was revised to state, "Although the device can operate at 1.2 V core voltage, the device can only be reprogrammed when all supplies (VCC, VCCI, and VJTAG) are at 1.5 V."	327
	The "ISP Support in Flash-Based Devices" section and Table 13-1 • Flash-Based FPGAs Supporting ISP were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	328
	The "Security" section was updated to mention that 15 k gate devices do not have a built-in 128-bit decryption core.	330
	Table 13-2 • Power Supplies was revised to remove the Normal Operation column and add a table note stating, "All supply voltages should be at 1.5 V or higher, regardless of the setting during normal operation."	329
	The "ISP Programming Header Information" section was revised to change FP3-26PIN-ADAPTER to FP3-10PIN-ADAPTER-KIT. Table 13-3 • Programming Header Ordering Codes was updated with the same change, as well as adding the part number FFSD-05-D-06.00-01-N, a 10-pin cable with 50-mil-pitch sockets.	335
	The "Board-Level Considerations" section was updated to describe connecting two capacitors in parallel across VPUMP and GND for proper programming.	337
v1.0 (January 2008)	Information was added to the "Programming Voltage (VPUMP) and VJTAG" section about the JTAG interface pin.	329
51900055-2/7.06	ACTgen was changed to SmartGen.	N/A
	In Figure 13-6 • Board Layout and Programming Header Top View, the order of the text was changed to: VJTAG from the target board VCCI from the target board	337
	VCC from the target board	

# 16 – Boundary Scan in Low Power Flash Devices

## **Boundary Scan**

Low power flash devices are compatible with IEEE Standard 1149.1, which defines a hardware architecture and the set of mechanisms for boundary scan testing. JTAG operations are used during boundary scan testing.

The basic boundary scan logic circuit is composed of the TAP controller, test data registers, and instruction register (Figure 16-2 on page 360).

Low power flash devices support three types of test data registers: bypass, device identification, and boundary scan. The bypass register is selected when no other register needs to be accessed in a device. This speeds up test data transfer to other devices in a test data path. The 32-bit device identification register is a shift register with four fields (LSB, ID number, part number, and version). The boundary scan register observes and controls the state of each I/O pin. Each I/O cell has three boundary scan register cells, each with serial-in, serial-out, parallel-in, and parallel-out pins.

## **TAP Controller State Machine**

The TAP controller is a 4-bit state machine (16 states) that operates as shown in Figure 16-1.

The 1s and 0s represent the values that must be present on TMS at a rising edge of TCK for the given state transition to occur. IR and DR indicate that the instruction register or the data register is operating in that state.

The TAP controller receives two control inputs (TMS and TCK) and generates control and clock signals for the rest of the test logic architecture. On power-up, the TAP controller enters the Test-Logic-Reset state. To guarantee a reset of the controller from any of the possible states, TMS must remain HIGH for five TCK cycles. The TRST pin can also be used to asynchronously place the TAP controller in the Test-Logic-Reset state.

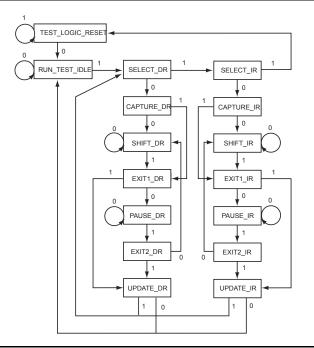


Figure 16-1 • TAP Controller State Machine

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Power-Up/-Down Behavior of Low Power Flash Devices

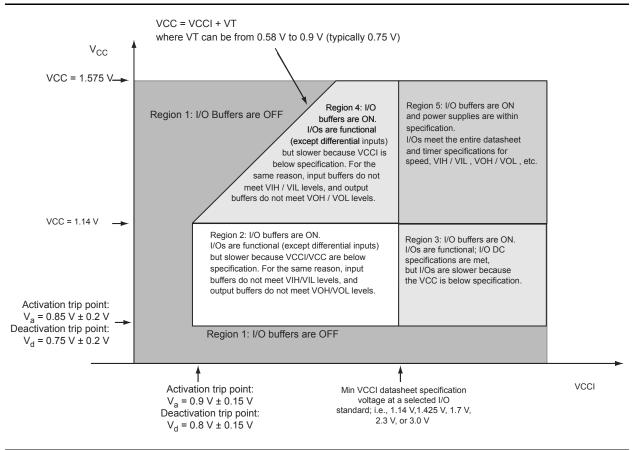


Figure 18-5 • I/O State as a Function of VCCI and VCC Voltage Levels for IGLOO V2, IGLOO nano V2, IGLOO PLUS V2, and ProASIC3L Devices Running at VCC = 1.2 V ± 0.06 V



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